



MEMC 99-0900 (2632)
PATENT

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5/25/02

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application of Fuerhoff et al.

Art Unit 1765

Serial No. 09/502,340

Filed February 10, 2000

Confirmation No. 5009

For METHOD OF CONTROLLING DIAMETER OF A SILICON CRYSTAL IN A
LOCKED SEED LIFT GROWTH PROCESS (as amended by Amendment A)

Examiner M. Anderson

May 17, 2002

AMENDMENT C UNDER 37 CFR § 1.116

TO THE ASSISTANT COMMISSIONER FOR PATENTS,

SIR:

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In response to the final Office action mailed February 20, 2002 (Paper No. 9), and the Advisory action mailed April 29, 2002 (Paper No. 11), and the telephone interview conducted with the undersigned on May 14, 2002, please enter the following amendments:

IN THE CLAIMS

Please amend claims 1 and 9 as follows:

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- 5 1. A method for use in combination with a crystal growing apparatus for growing a monocrystalline ingot according to the Czochralski process, said crystal growing apparatus having a heated crucible containing a semiconductor melt from which the ingot is grown, said ingot being grown on a seed crystal pulled from the melt, said method comprising the steps of:
- 5 defining a temperature model representative of variations in the temperature of the melt in response to variations in power supplied to a heater for heating the melt;